N-Channel Junction Silicon FET





2026

## **Capacitor Microphone Applications**

**€**1393A

## **Features**

- . Especially suited for use in audio, telephone capacitor microphones.
- . High |yfs|.
- . Excellent voltage characteristic.

Absolute Maximum Ratings at Ta	:=25 <sup>0</sup> C		•	•	unit
Gate-Drain Voltage	$v_{\rm GDO}$			-20	٧
Gate Current	т.			10	mA
Allowable Power Dissipation	$P_{D}$			100	mΜ
Junction Temperature	Tj			125	°C
Storage Temperature	Tstg	•	-55 to	+125	ОC

Rlectrical Characteristics at Ta=25°C max unit Drian Current IDSS  $\mathtt{v}_{\mathtt{DS}}\mathtt{=5V},\mathtt{v}_{\mathtt{GS}}\mathtt{=0}$ **\***008

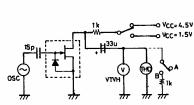
\*: The 2SK377 is classified by drain current  $\mathbf{I}_{DSS}$  as follows (unit:uA):

-	_	400	 ••	300	1		1 1	 000

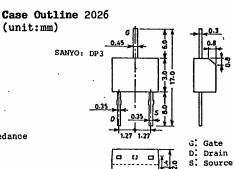
$[Ta=25^{\circ}C, V_{CC}=4.5V, R_{L}=1kohm, ein=15]$	pF,spe	ecified Test Circuit	min	<b>ty</b> p	max	unit
Transmission Loss	$G_{vr}$	f=1kHz,V <sub>in</sub> =100mV		-3.5		dΒ
Reduced Voltage Characteristic	∆Ğııı	$f=1kHz, V_{in}=100mV$			<del>-</del> 3	dΒ
	• • •	V <sub>CC</sub> =4.5 to 1.5V				
Frequency Response	△G <sub>Vf</sub>	f=1kHzto110Hz, Vin=100m	V		-1	ďΒ
Input Impedance	Zin	f=1kHz	18.0			Mohm
Output Impedance	Z	f=1kHz			1.0	kohm
Total Harmonic Distortion	THD	f=1kHz f=1kHz,V <sub>in</sub> =100mV		3		a %
Output Noise Voltage	v <sub>no</sub>	V <sub>in</sub> =0, A curve			-110	dB

## Specified Test Circuit

Transmission loss Frepuency response Distortion Reduced voltage characteristic

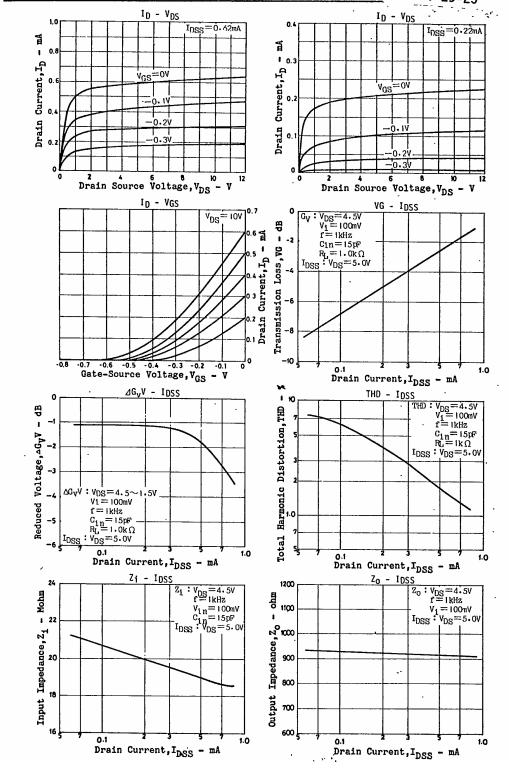


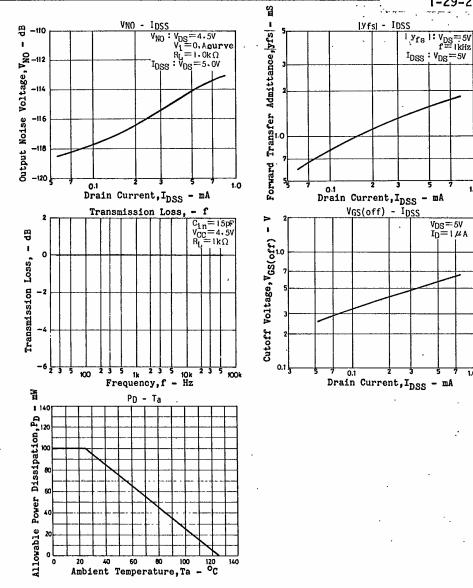
For output impedance



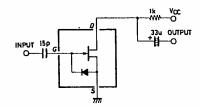








Sample Application Circuit: 2-wire type



## CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- ●All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- •All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

